



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel and P-Channel Silicon MOSFETs

MCH6660 — General-Purpose Switching Device Applications

Features

- ON-resistance Nch : $R_{DS(on)1}=105m\Omega$ (typ.)
Pch : $R_{DS(on)1}=205m\Omega$ (typ.)
- 1.8V drive
- Halogen free compliance

Specifications

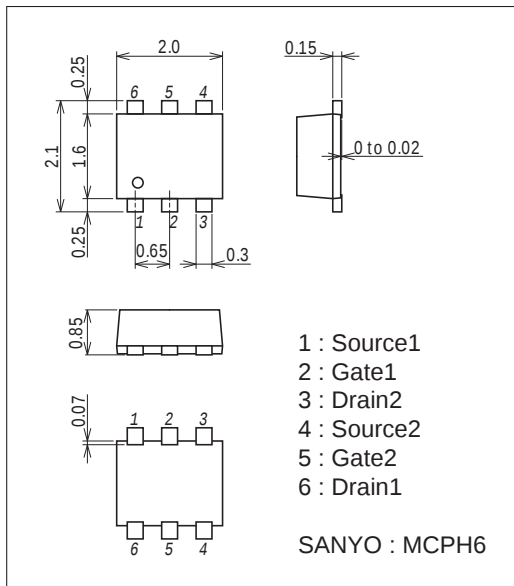
Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	N-channel	P-channel	Unit
Drain-to-Source Voltage	V_{DSS}		20	-20	V
Gate-to-Source Voltage	V_{GSS}		± 10	± 10	V
Drain Current (DC)	I_D		2	-1.5	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	8	-6	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate ($900mm^2 \times 0.8mm$) 1unit	0.8		W
Channel Temperature	T_{ch}		150		$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150		$^\circ\text{C}$

Package Dimensions

unit : mm (typ)

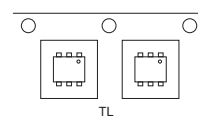
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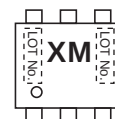
Product & Package Information

- Package : MCPH6
- JEITA, JEDEC : SC-88, SOT-363
- Minimum Packing Quantity : 3,000 pcs./reel

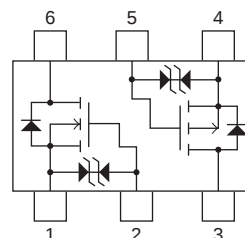
Packing Type : TL



Marking



Electrical Connection



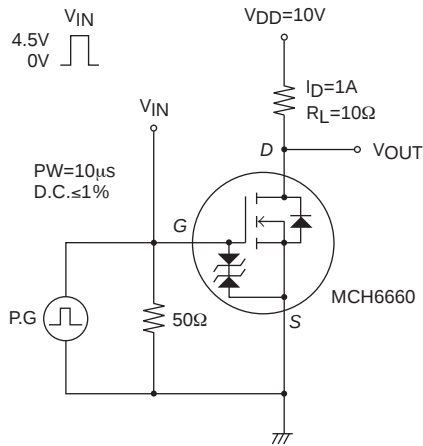
MCH6660

Electrical Characteristics at Ta=25°C

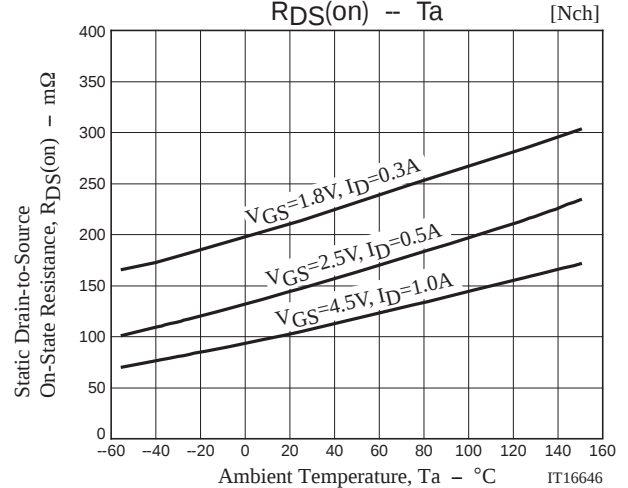
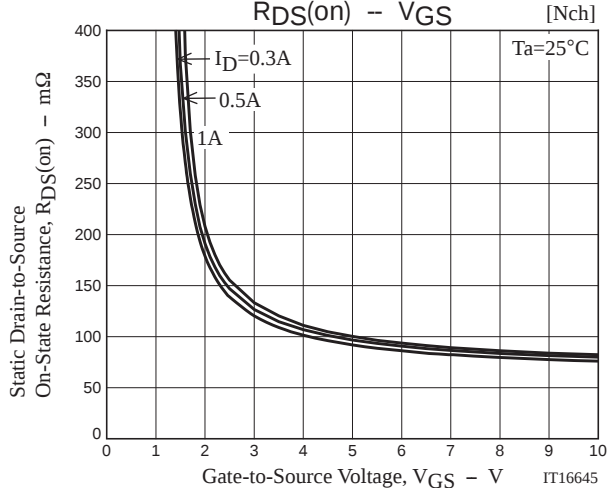
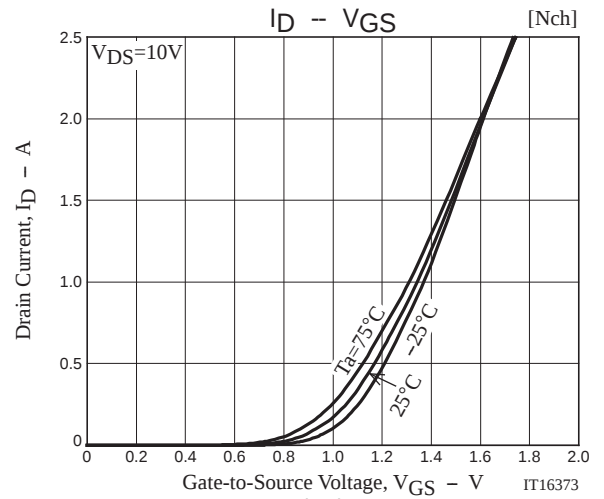
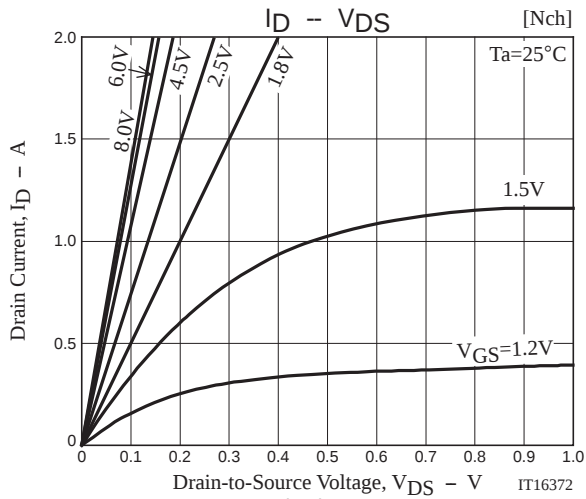
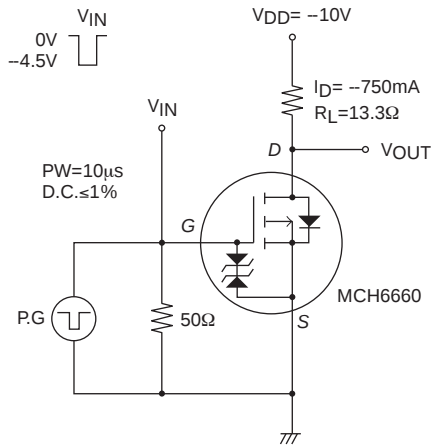
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	VDS=20V, VGS=0V			1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	VDS=10V, ID=1A		1.9		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=1A, VGS=4.5V		105	136	mΩ
	RDS(on)2	ID=0.5A, VGS=2.5V		147	205	mΩ
	RDS(on)3	ID=0.3A, VGS=1.8V		212	318	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		128		pF
Output Capacitance	Coss			28		pF
Reverse Transfer Capacitance	Crss			21		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		5.1		ns
Rise Time	tr			11		ns
Turn-OFF Delay Time	td(off)			14.5		ns
Fall Time	tf			12		ns
Total Gate Charge	Qg	VDS=10V, VGS=4.5V, ID=2A		1.8		nC
Gate-to-Source Charge	Qgs			0.3		nC
Gate-to-Drain “Miller” Charge	Qgd			0.55		nC
Diode Forward Voltage	VSD	IS=2A, VGS=0V		0.85	1.2	V
[P-channel]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V
Zero-Gate Voltage Drain Current	IDSS	VDS=-20V, VGS=0V			-1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=-10V, ID=-1mA	-0.4		-1.4	V
Forward Transfer Admittance	yfs	VDS=-10V, ID=-750mA		1.9		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-750mA, VGS=-4.5V		205	266	mΩ
	RDS(on)2	ID=-300mA, VGS=-2.5V		295	413	mΩ
	RDS(on)3	ID=-100mA, VGS=-1.8V		430	645	mΩ
Input Capacitance	Ciss	VDS=-10V, f=1MHz		120		pF
Output Capacitance	Coss			26		pF
Reverse Transfer Capacitance	Crss			20		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		5.3		ns
Rise Time	tr			9.7		ns
Turn-OFF Delay Time	td(off)			16		ns
Fall Time	tf			14		ns
Total Gate Charge	Qg	VDS=-10V, VGS=-4.5V, ID=-1.5A		1.7		nC
Gate-to-Source Charge	Qgs			0.28		nC
Gate-to-Drain “Miller” Charge	Qgd			0.47		nC
Diode Forward Voltage	VSD	IS=-1.5A, VGS=0V		-0.89	-1.2	V

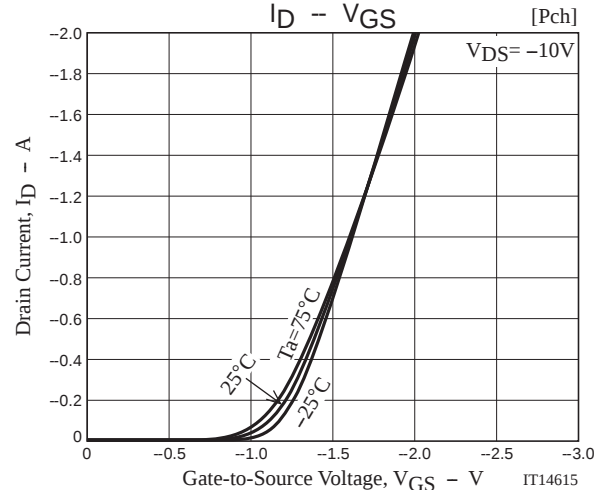
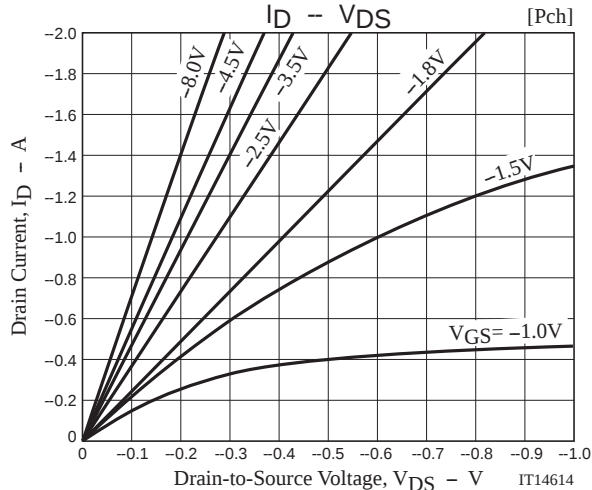
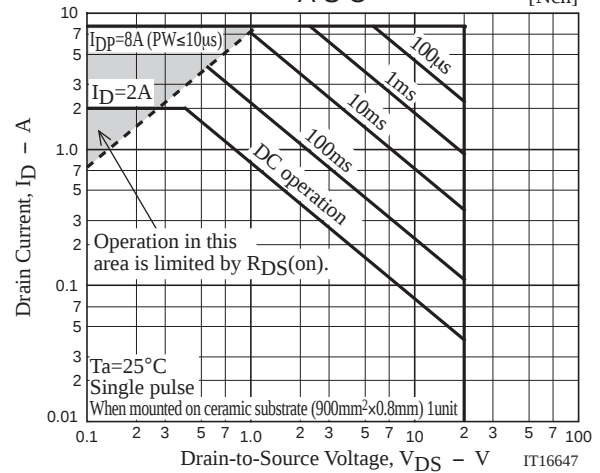
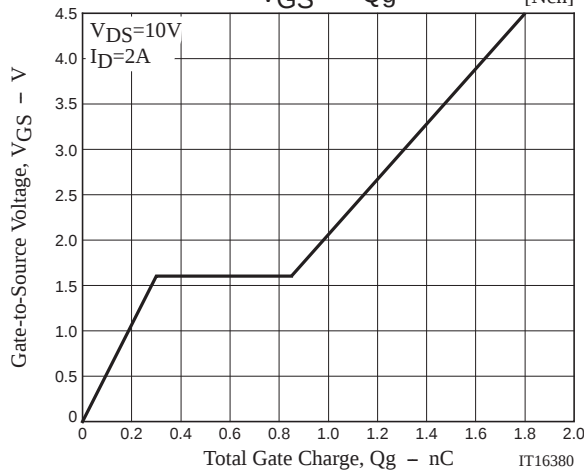
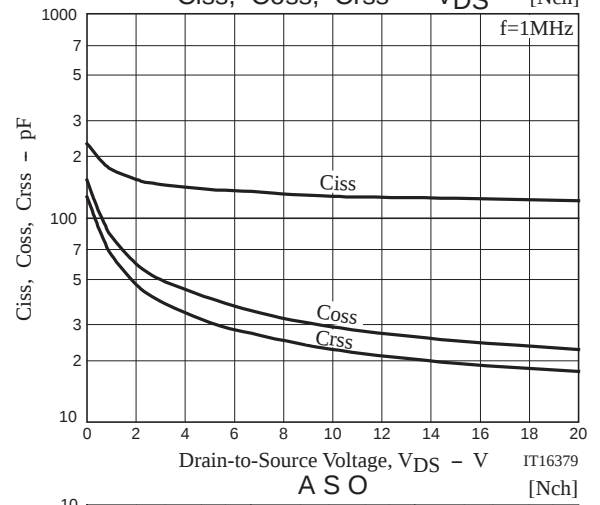
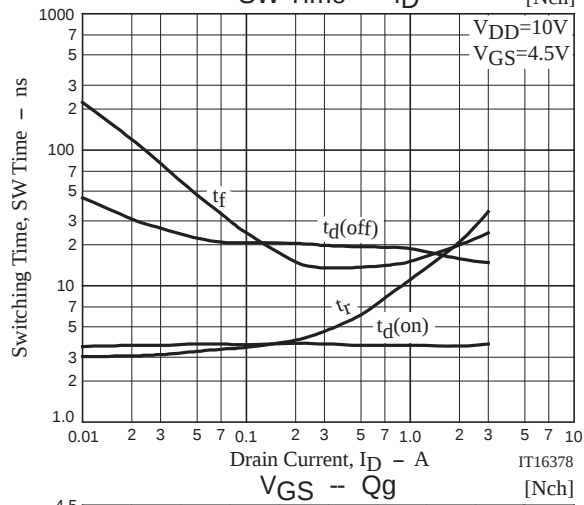
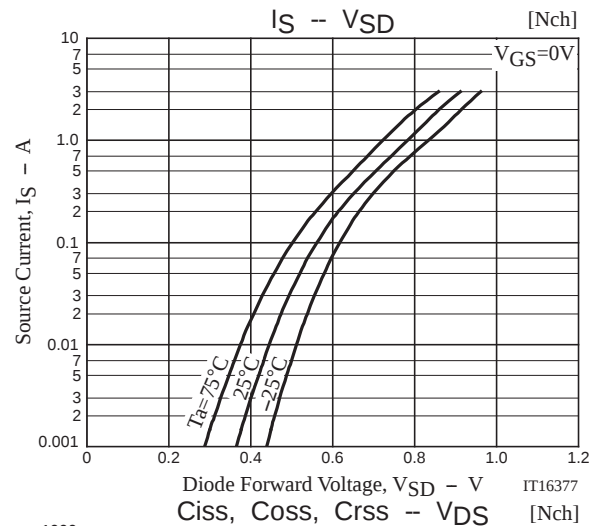
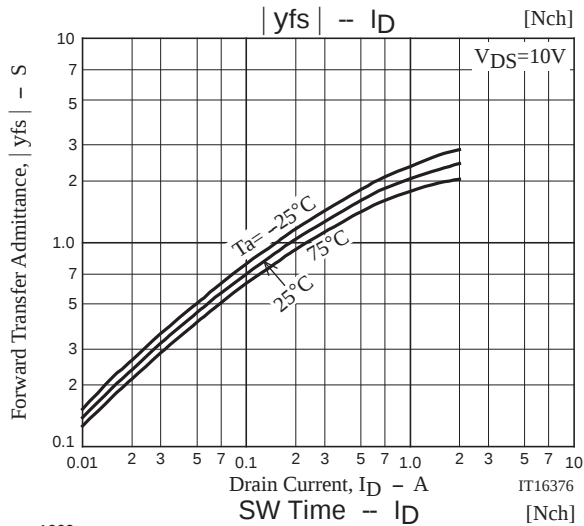
Switching Time Test Circuit

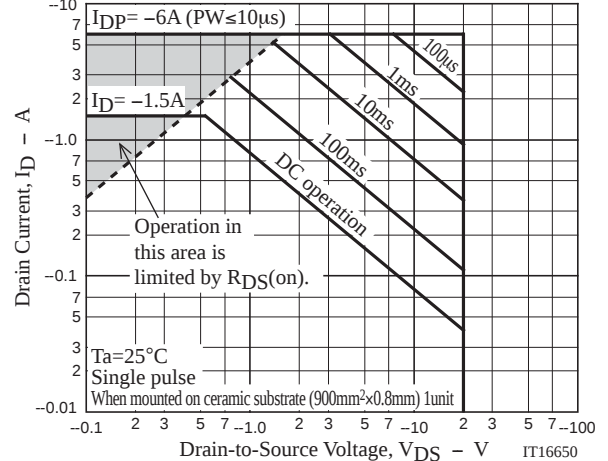
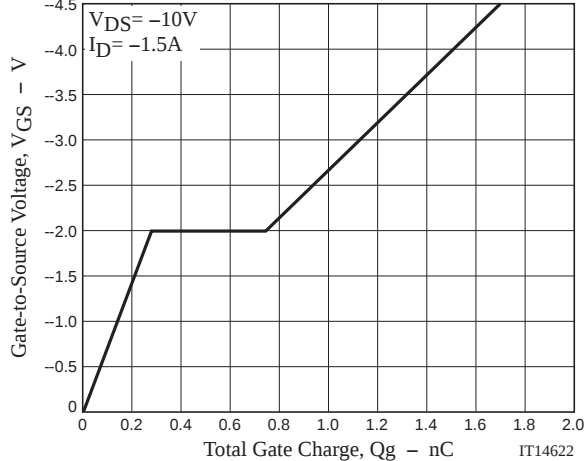
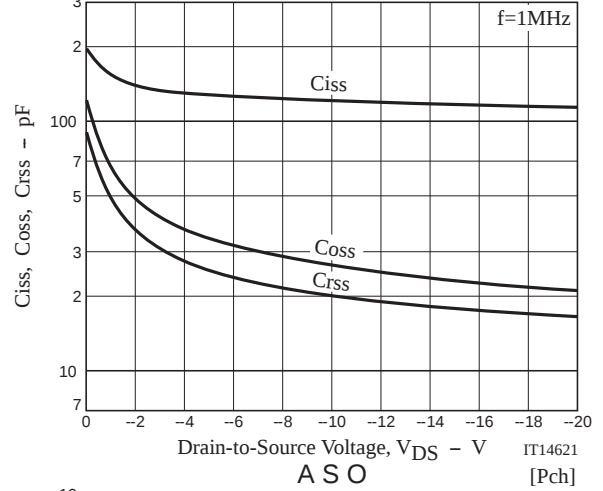
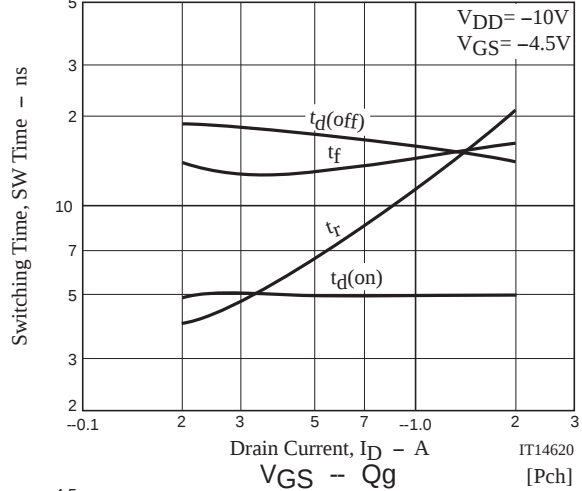
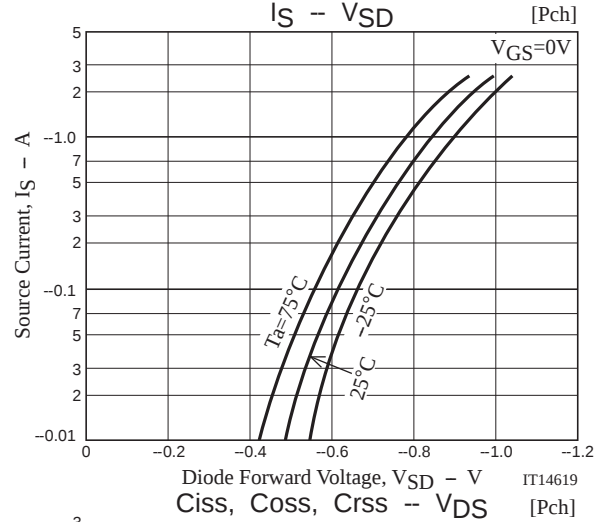
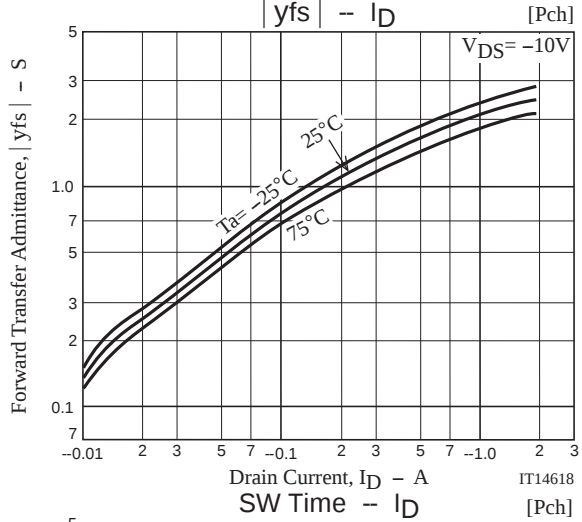
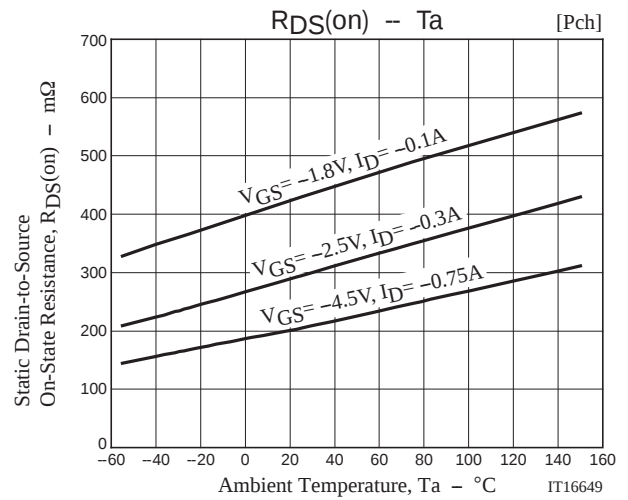
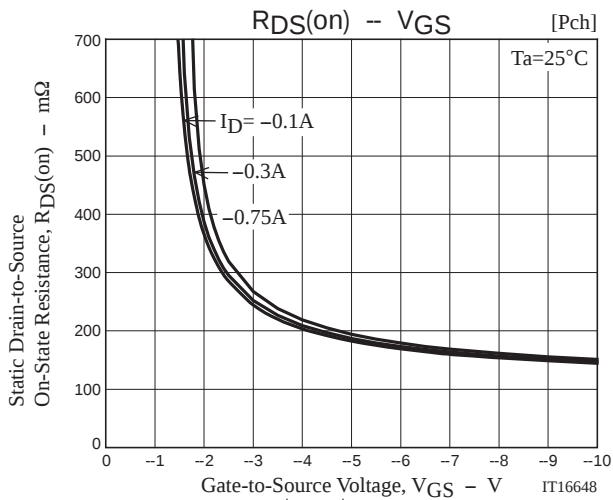
[N-channel]

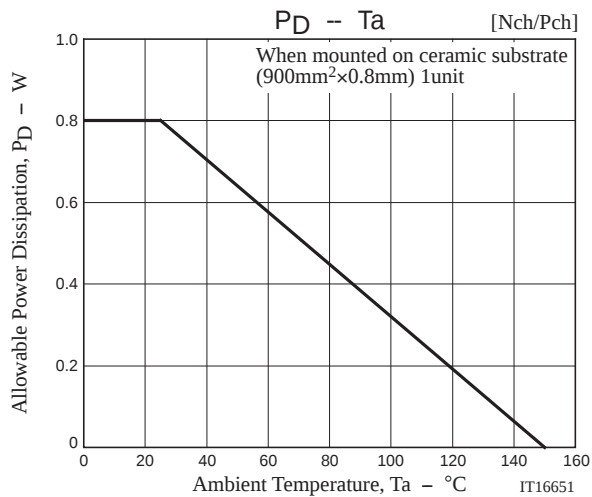


[P-channel]









Note on usage : Since the MCH6660 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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